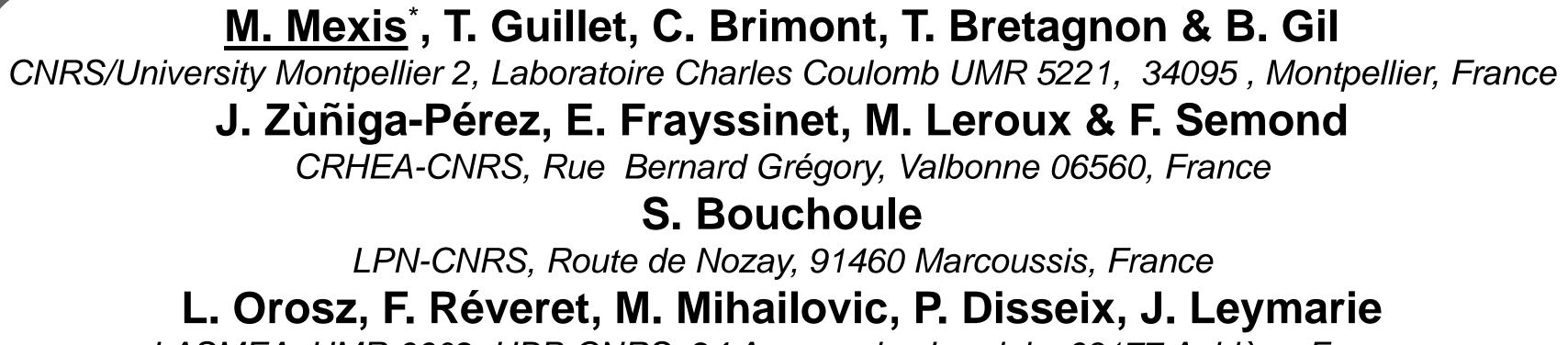


## **Polariton with high quality factor** in a hybrid ZnO-based microcavity



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ZnO based microcavities are exhibiting very well defined excitonic features with a large ratio of the vacuum Rabi splitting to the polariton linewidth, and a large exciton binding energy which make them suitable for room temperature polariton lasers. However, a main drawback in order to obtain cavities with high Quality factor (Q) values is the intense strain in AlGaN/AIN DBRs limiting the ability of growing large number of AlGaN/AIN pairs. Here, we propose an alternative way for achieving high Q values by introducing a new hybrid-type ZnO-based planar microcavity. Compared to other reported oxide cavities, the good crystal quality of the active layer can be achieved by growing the ZnO on top of AlN. We explore the microcavity by performing μ-Photoluminescence (μ-PL) and μ-Reflectivity experiments mapping in micron scale the polariton branch on the sample surface.

Si<sub>x</sub>N<sub>y</sub>

SiO,

AIN

**AlGaN** 

ZnO

SiO,

Si<sub>x</sub>N<sub>y</sub>

Al

**Pyrex** 

Growth on AIN (invert cavity)

- (x 10)

<sup>-</sup> (x 3.5)

<sup>–</sup> (x 3.0)

47

## **New process for larger Q values**

**Pyrex** 

Al mirror

Si<sub>x</sub>N<sub>y</sub>

SiO<sub>2</sub>

ZnO (lambda/2)

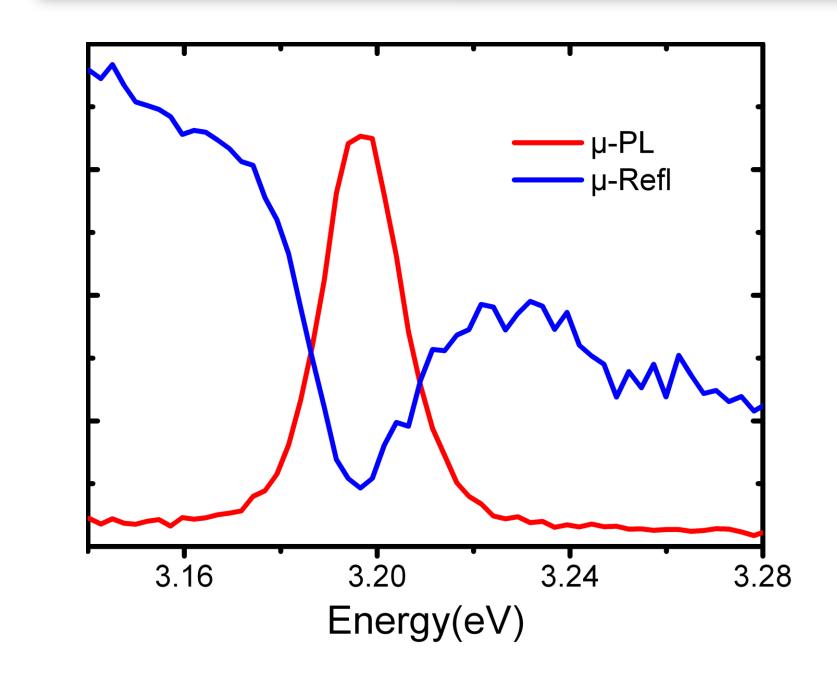
AlGaN

AIN

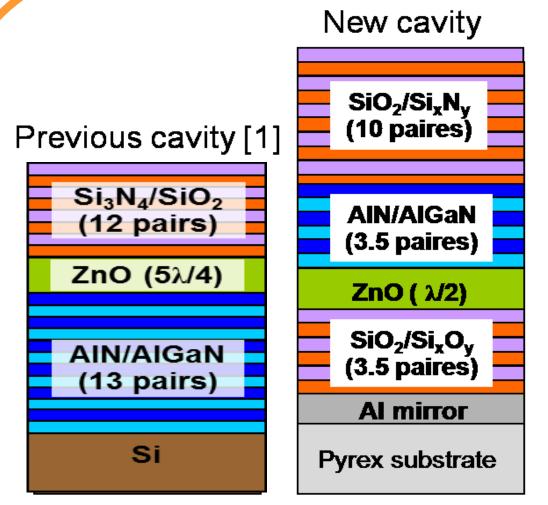
Etching of Si

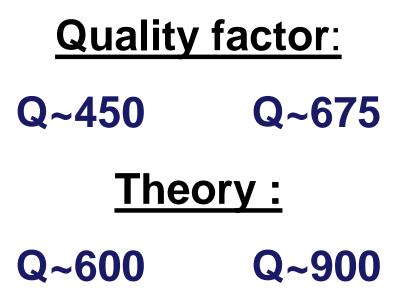


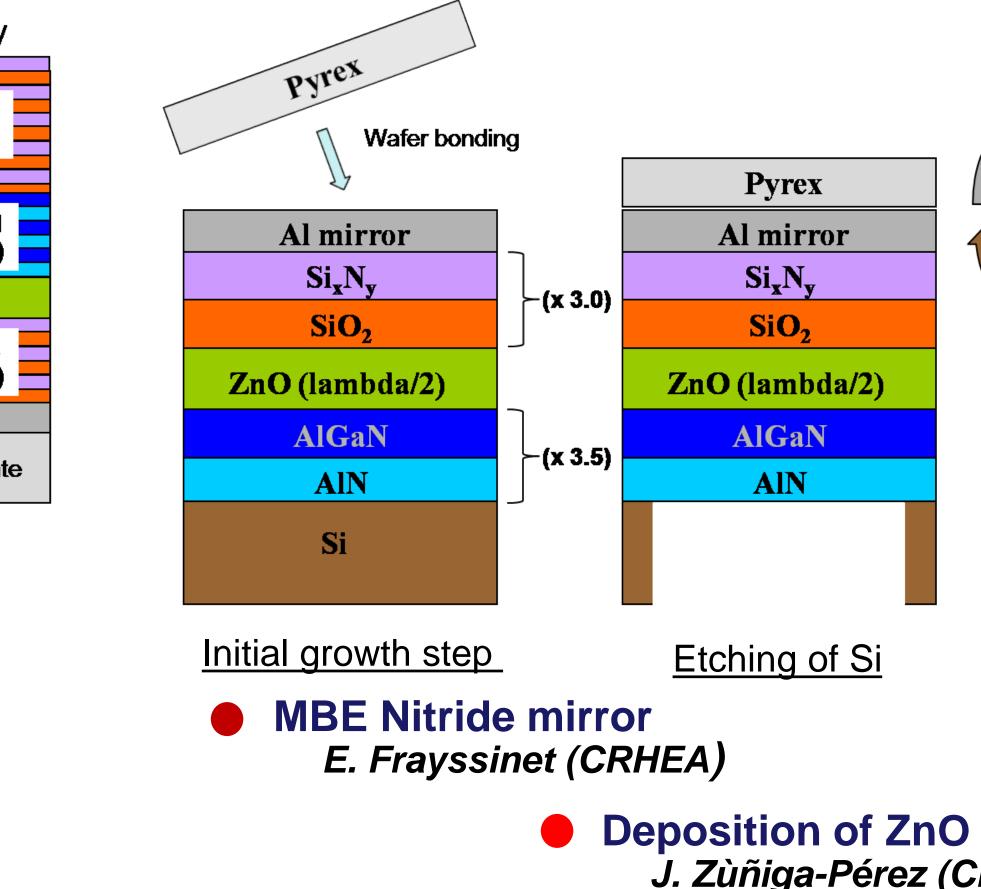
μ- Photoluminescence & μ-**Reflectivity at 300K** 



 $\mu$ -PL and  $\mu$ -reflectivity spectra show the low branch polariton around ~3.20eV









J. Zùñiga-Pérez (CRHEA) **RF-PECVD SiO2/Si<sub>x</sub>N<sub>y</sub>** S. Bouchoule (LPN)

